

# PEMH30; PUMH30

NPN/NPN double resistor-equipped transistors;  
R1 = 2.2 k $\Omega$ , R2 = open

Rev. 01 — 28 March 2006

Product data sheet

## 1. Product profile

### 1.1 General description

NPN/NPN double Resistor-Equipped Transistors (RET) in Surface Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package		NPN/PNP complement	PNP/PNP complement
	Philips	JEITA		
PEMH30	SOT666	-	PEMD30	PEMB30
PUMH30	SOT363	SC-88	PUMD30	PUMB30

### 1.2 Features

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Cost-saving alternative for BC847BS and BC847BV

### 1.4 Quick reference data

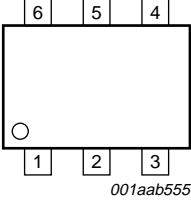
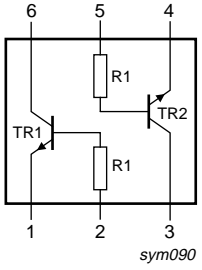
Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	50	V
I <sub>O</sub>	output current		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	k $\Omega$

**PHILIPS**

## 2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1		

## 3. Ordering information

Table 4. Ordering information

Type number	Package		Version
	Name	Description	
PEMH30	-	plastic surface mounted package; 6 leads	SOT666
PUMH30	SC-88	plastic surface mounted package; 6 leads	SOT363

## 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMH30	2S
PUMH30	*B1

[1] \* = -: made in Hong Kong  
 \* = p: made in Hong Kong  
 \* = t: made in Malaysia  
 \* = W: made in China

## 5. Limiting values

**Table 6. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
<b>Per transistor</b>						
V <sub>CBO</sub>	collector-base voltage	open emitter	-	50	V	
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V	
V <sub>EBO</sub>	emitter-base voltage	open collector	-	5	V	
I <sub>O</sub>	output current		-	100	mA	
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	100	mA	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C				
	SOT363		[1]	-	200	mW
	SOT666		[1][2]	-	200	mW
<b>Per device</b>						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C				
	SOT363		[1]	-	300	mW
	SOT666		[1][2]	-	300	mW
T <sub>j</sub>	junction temperature		-	150	°C	
T <sub>amb</sub>	ambient temperature		-65	+150	°C	
T <sub>stg</sub>	storage temperature		-65	+150	°C	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

## 6. Thermal characteristics

**Table 7. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air				
	SOT363		[1]	-	625	K/W
	SOT666		[1][2]	-	625	K/W
<b>Per device</b>						
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air				
	SOT363		[1]	-	416	K/W
	SOT666		[1][2]	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

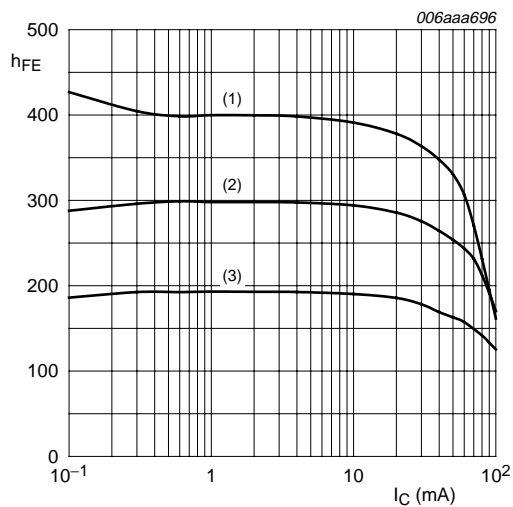
[2] Reflow soldering is the only recommended soldering method.

7. Characteristics

Table 8. Characteristics

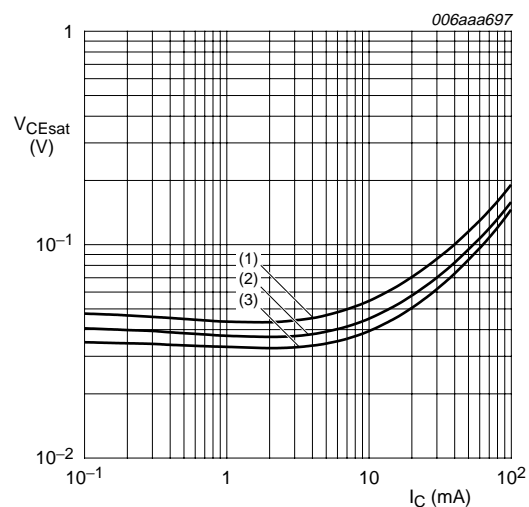
T<sub>amb</sub> = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A	-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A	-	-	1	μA
		V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 20 mA	30	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA	-	-	150	mV
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = i <sub>e</sub> = 0 A; f = 1 MHz	-	-	2.5	pF



V<sub>CE</sub> = 5 V  
 (1) T<sub>amb</sub> = 100 °C  
 (2) T<sub>amb</sub> = 25 °C  
 (3) T<sub>amb</sub> = -40 °C

Fig 1. DC current gain as a function of collector current; typical values



I<sub>C</sub>/I<sub>B</sub> = 20  
 (1) T<sub>amb</sub> = 100 °C  
 (2) T<sub>amb</sub> = 25 °C  
 (3) T<sub>amb</sub> = -40 °C

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values

8. Package outline

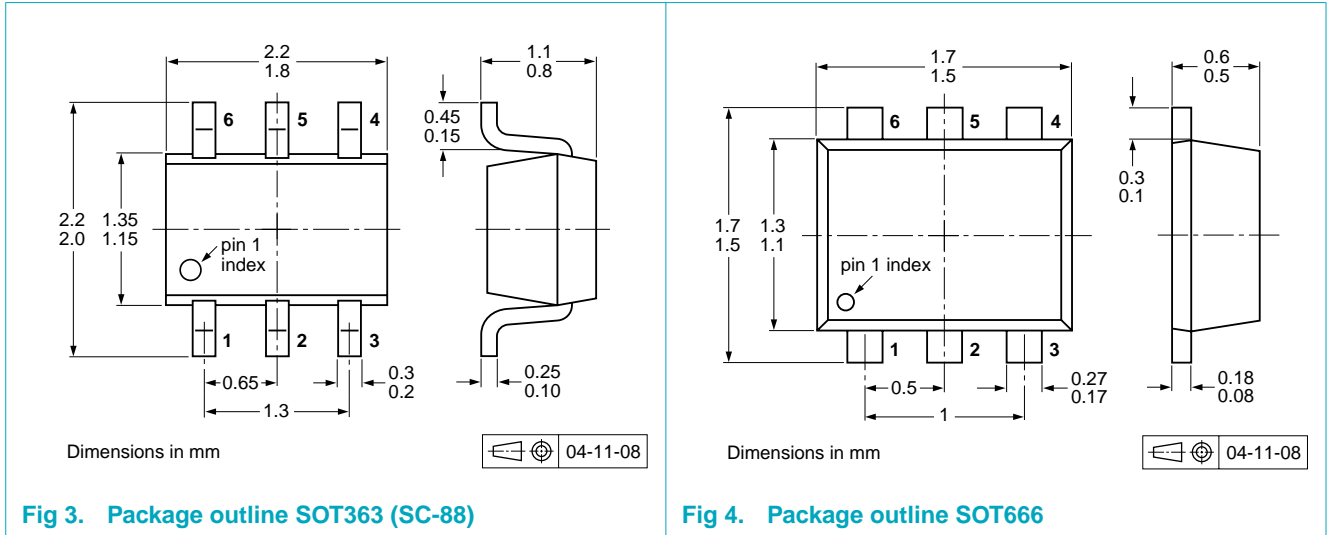


Fig 3. Package outline SOT363 (SC-88)

Fig 4. Package outline SOT666

9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

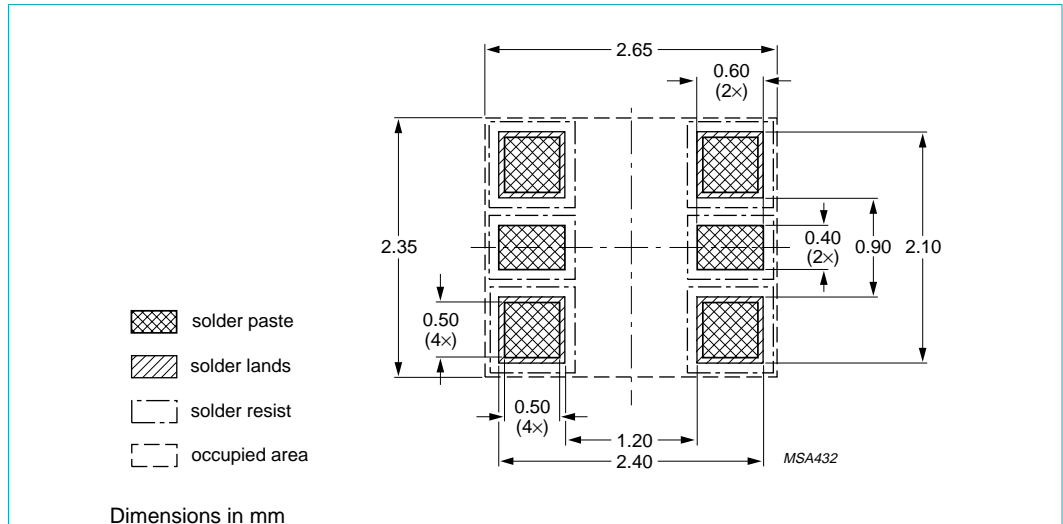
Type number	Package	Description	Packing quantity			
			3000	4000	8000	10000
PEMH30	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PUMH30	SOT363	4 mm pitch, 8 mm tape and reel; T1 <sup>[2]</sup>	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2 <sup>[3]</sup>	-125	-	-	-165

[1] For further information and the availability of packing methods, see [Section 13](#).

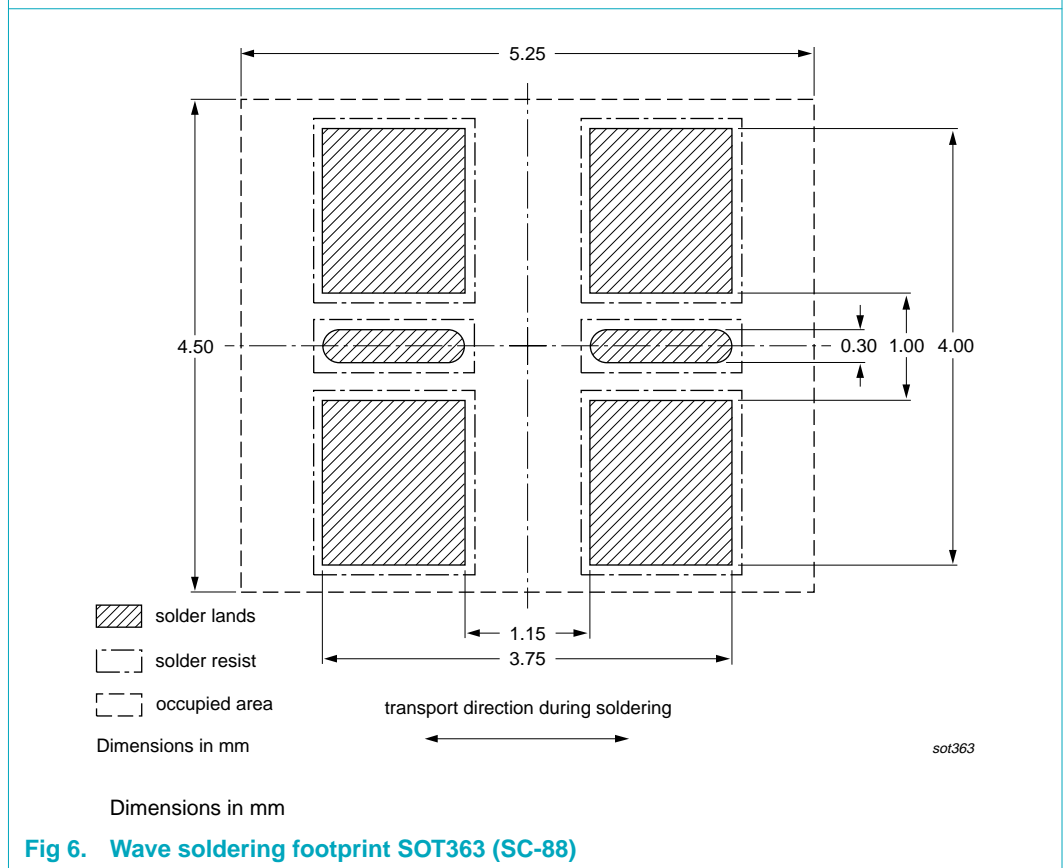
[2] T1: normal taping

[3] T2: reverse taping

**10. Soldering**



**Fig 5. Reflow soldering footprint SOT363 (SC-88)**



**Fig 6. Wave soldering footprint SOT363 (SC-88)**

